

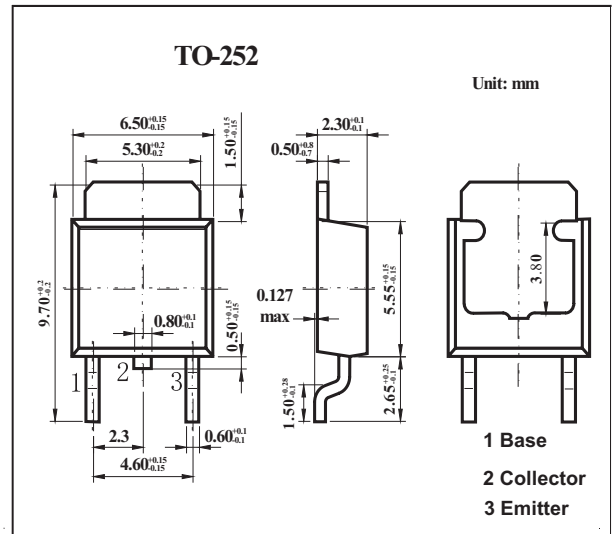
TO-252 Plastic-Encapsulate Transistors

FEATURES

- PNP TRANSISTORS
- Collector-Base Voltage: $V_{CB0}=-40V$
- Low Speed Switching

MECHANICAL DATA

- Case style:TO-252 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CB0}	Collector-Base Voltage	-40	V
V_{CE0}	Collector-Emmitter Voltage	-30	V
V_{EB0}	Emmitter-Base Voltage	-6	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	100	°C/W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

PACKAGE INFORMATION

Device	Package	Shipping
2SB772	TO-252	500/Tape&Reel

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CB0}$	$I_C=-100\mu A, I_E=0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CE0}$	$I_C=-10mA, I_B=0$	-30			V
Emmitter-base breakdown voltage	$V_{(BR)EB0}$	$I_E=-100\mu A, I_C=0$	-6			V
Collector cut-off current	I_{CB0}	$V_{CB}=-40V, I_E=0$			-1	μA
Collector cut-off current	I_{CE0}	$V_{CE}=-30V, I_B=0$			-10	μA
Emmitter cut-off current	I_{EB0}	$V_{EB}=-6V, I_C=0$			-1	μA
DC current gain	h_{FE}	$V_{CE}=-2V, I_C=-1A$	60		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-0.2A$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-2A, I_B=-0.2A$			-1.5	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-0.1A$ $f=10MHz$	50	80		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400